## Crosslinked Ion-conducting Hybrid Coating Layers for Robust Artificial Solid-electrolyte Interphase Towards High-Performance Silicon Anodes

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3 Fig. S1. TGA curves of Si@PL-10 and SiNPs



5 Fig. S2 HRTEM image of Si@PAA particles.



Fig. S3. SEM image of Si@PL-10 particles and the corresponding EDS Mapping results.
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7 Fig. S5. Nyquist plots of (a) pure Si, (b) Si@PAA electrode after 10, 20, 50, and 100 cycles at
8 1 A/g. (c) Impedance of different Si electrodes at varied cycles. Warburg impedance plots at
9 low frequency after (d) 10 cycles and 20 cycles and (e) 50 cycles and 100 cycles.



5 Fig. S6. (a) Galvanostatic intermittent titration technique (GITT) curves of Si@PL-10, 6 Si@PAA and pure Si in both charge and discharge processes. (b) The Li-ion diffusion 7 coefficients ( $D_{Li^+}$ ) during the charge process calculated from the GITT profile.



9 Fig. S7. Ex-situ XPS spectra of the Si@PL-10 electrode on the initial cycle. (a) C 1s spectra,
10 (b) O1s spectra, (c) F 1s spectra.



- 2 Fig. S8. Top-viewed SEM images of various Si electrodes before cycling. (a) Si@PL-10, (b)
- 3 Si@PAA, and (c) pure Si. AFM images of surface morphology of various Si electrodes before
- 4 cycling. (d) Si@PL-10, (e) Si@PAA, and (f) pure Si. Cross-sectional SEM images of various
- 5 Si electrodes before cycling. (g) Si@PL-10, (h) Si@PAA, and (i) pure Si.



Fig. S9. FTIR spectra of the SiNPs, PAA, PL-10, Si@PL-5, Si@PL-10 and Si@PL-15

 $D_{Li^{+}} = \frac{R^2 T^2}{2A^2 n^4 F^4 C^2 \sigma^2}$ (1)

3 Equation S1. Where R is the gas phase constant, T is room temperature, A is the surface area 4 of the electrode, n (1) is the charge transfer number, F is the Faraday constant (9.6486×10<sup>4</sup>), C 5 is the Li<sup>+</sup> concentration in the Si electrode,  $\sigma$  is the Warburg coefficient, which is the slope of 6 the lines depicted in  $\omega^{-1/2}$ -Z'.

$D_{Li^{+}} = \frac{4}{\pi \tau} \left( \frac{n_M V_M}{S} \right)^2 \left( \frac{\Delta E_s}{\Delta E_s} \right)^2$	(2)
$(-\tau)$	(2)

15 Equation S2. where  $\tau$  represents the pulse time (600 s),  $n_M$  is the number of moles,  $V_M$  is the 16 molar volume of the active material, S stands for the electrode-electrolyte contact area (1.13 17 cm<sup>-2</sup>),  $\Delta E_S$  is the potential change at the end of two subsequent relaxation periods,  $\Delta E_{\tau}$ 18 represents the potential change during the current pulse.<sup>1</sup>

	-			8
		Si@PL-10	Si@PAA	Pure Si
	R <sub>s</sub>	2.078	3.089	2.827
10th	R <sub>SEI</sub>	0.579	0.785	1.569
	R <sub>CT</sub>	2.842	3.313	4.84
	R <sub>s</sub>	2.06	2.588	2.144
20th	R <sub>SEI</sub>	1.754	1.945	2.578
	R <sub>CT</sub>	2.956	3.467	7.125
	R <sub>s</sub>	2.137	3.359	2.262
50th	R <sub>SEI</sub>	1.998	5.084	7.255
	R <sub>CT</sub>	2.499	3.218	7.249
	R <sub>s</sub>	2.192	2.944	3.821
100th	R <sub>SEI</sub>	4.94	7.547	11.35
	R <sub>CT</sub>	3.069	6.851	7.243

3 Table S1. The corresponding resistance [ohm] results obtained by fitting to the circuit.

5 Table S2. The calculated  $D_{Li^+}$  [cm<sup>2</sup> s<sup>-1</sup>] from electrochemical impedance analysis.

Electrode	10th	20th	50th	100th
Si@PL-10	6.03E-12	6.1E-12	6.67E-12	4.58E-12
Si@PAA	5.27E-12	4.71E-12	4.47E-12	2.12E-12
Pure Si	5.13E-12	2.38E-12	2.39E-12	2E-12

Materials	Cycle stability (mAh g <sup>-1</sup> )		Rate performa nce (mAh g <sup>-1</sup> )	Ref.
Si@PL-10	1.0 A g <sup>-1</sup> 2297 (200th)	4.0 A g <sup>-1</sup> 1978 (100th)	6.0 A g <sup>-1</sup> 1905	This work
SiO <sub>x</sub> /C@void@Si/C	0.20 A g <sup>-1</sup> 1094 (550th)	5.0 A g <sup>-1</sup> 351 (2000th)	5.0 A g <sup>-1</sup> 450	2
B-3DCF/Si@C	0.40 A g <sup>-1</sup> 1288.5 (600th)	1.0 A g <sup>-1</sup> 1084.3 (800th)	2.0 A g <sup>-1</sup> 988	3
Si@TTFPB 3%	0.84 A g <sup>-1</sup> 1778.7 (500th)	/	42 A g <sup>-1</sup> 1869.4	4
Si@PP	1.0 A g-1 1295 (300th)	4.0A g <sup>-1</sup> 1718 (60th)	8.0 A g <sup>-1</sup> 1333	5
Si@PP@CA	0.2 A g <sup>-1</sup> 2530 (100 th)	1 A g <sup>-1</sup> 1590 (100 th)	3.2 A g <sup>-1</sup> 1606	6
Si@NC@SnO <sub>2</sub>	0.3 A g <sup>-1</sup> 1056 (200th)	2 A g <sup>-1</sup> 510.7 (100th)	2 A g <sup>-1</sup> 764.1	7
Si@void@mes o-C	$0.42 \text{ A g}^{-1} \\ 1250 \\ (100 \text{ th})$	$\begin{array}{c} 0.42 \ {\rm A} \ {\rm g}^{\text{-1}} \\ 1250 \\ (150 \ {\rm th}) \end{array}$	4.2 A g <sup>-1</sup> 720	8
Si@SA@Borax	0.5 A g <sup>-1</sup> 1655.8 (500th)	/	/	9
Si@FG/C	0.2 A g <sup>-1</sup> 510 (100 th)	0.2 A g <sup>-1</sup> 500 (150 th)	5 A g <sup>-1</sup> 200	10
Si@C core-shell na- nocomposite	1.26 A g <sup>-1</sup> 1040 (100 th)	$1.26 \text{ A g}^{-1} \\ 1030 \\ (150 \text{ th})$	/	11

3	Table S3. A comparison of cycle stability and rate performance between th	e Si@PL-10
4	electrode and the other representatively reported Si anodes for LIBs.	

Si@C	2.1 A g <sup>-1</sup> 1150 (100 th)	/	/	12
Si@10C	0.5 A g <sup>-1</sup> 1500 (150 th)	/	/	13
si@AC/OC	0.36 A g <sup>-1</sup> 1250 (150 th)	/	7.2 A g <sup>-1</sup> 200	14
H-SiLC-2	1 A g <sup>-1</sup> 1250 (150 th)	2 A g <sup>-1</sup> 1240 (100 th)	5 A g <sup>-1</sup> 1200	15
Si@CMR	0.4 A g <sup>-1</sup> 1700 (120 th)	/	2 A g <sup>-1</sup> 1400	16
Si@PANI/SPA	1.2 A g <sup>-1</sup> 1500 (100 th)	/	4 A g <sup>-1</sup> 250	17
Si@SiO2@C	1 A g <sup>-1</sup> 800 (100 th)	/	/	18
Si-NP@	0.3 A g <sup>-1</sup> 1000 (150 th)	/	1.6 A g <sup>-1</sup> 900	19
SiNP@CT	/	/	8 A g <sup>-1</sup> 650	20

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